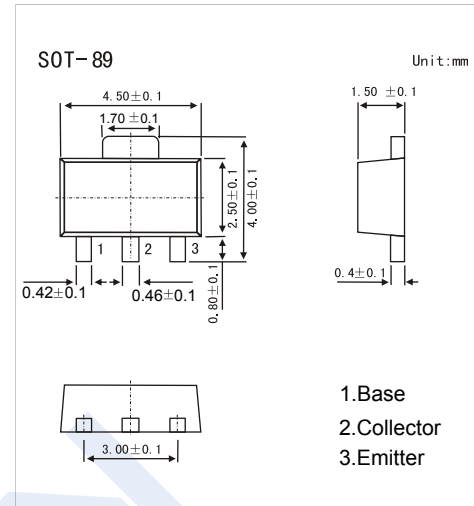


PNP Transistors

2SA1364

■ Features

- High Voltage $V_{CE0} = -60V$
- High Collector Current ($I_c = -1A$)
- High Collector Dissipation $P_c = 500mW$
- Small Package For Mounting
- Complementary to 2SC3444



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-60	V
Collector-Emitter Voltage	V_{CE0}	-60	V
Emitter-Base Voltage	V_{EB0}	-6	V
Collector Current	I_c	-1	A
Peak Collector Current	I_{CM}	-2	A
Collector Power Dissipation	P_c	500	mW
Jumction temperature	T_j	150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -100 \mu A, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -2 mA, I_B = 0$	-60			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_c = 0$	-6			nA
Collector-base cut-off current	I_{CB0}	$V_{CB} = -50 V, I_E = 0$			-200	
Emitter cut-off current	I_{EB0}	$V_{EB} = -4V, I_c = 0$			-200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -25mA$		-0.11	-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -25mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -4V, I_c = -100mA$	55		300	
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		22		pF
Transition frequency	f_T	$V_{CE} = -2V, I_E = 10mA$		85		MHz

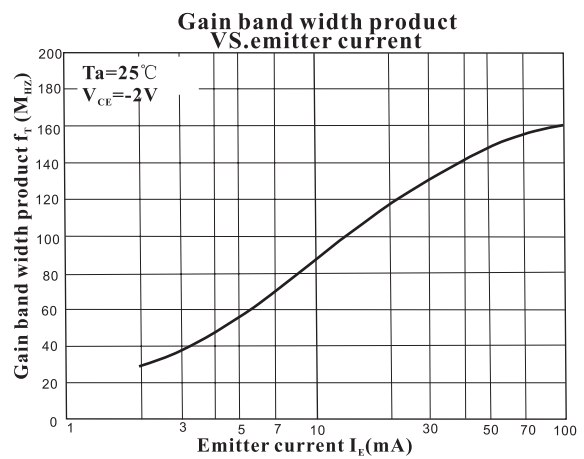
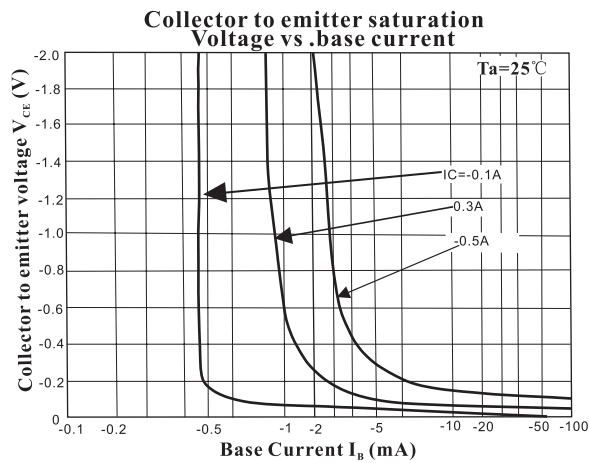
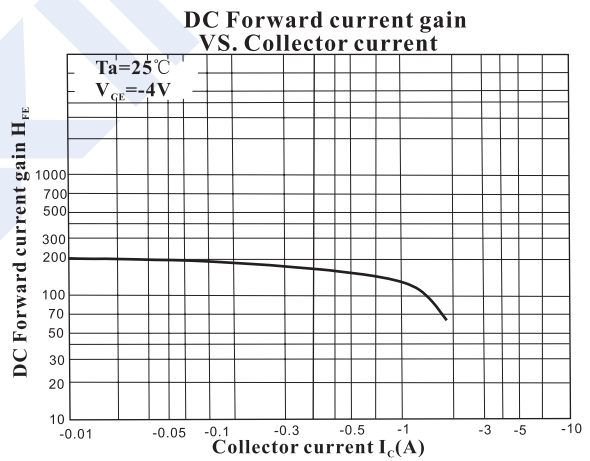
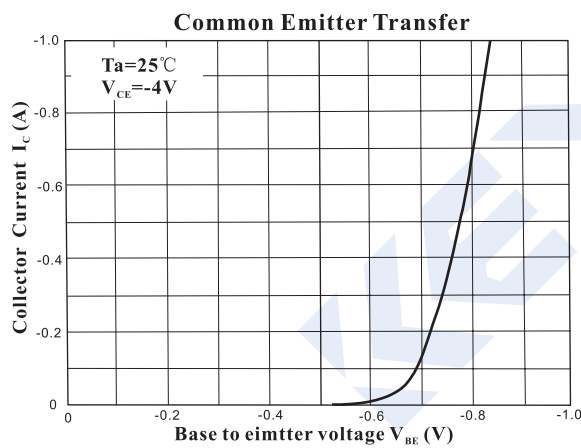
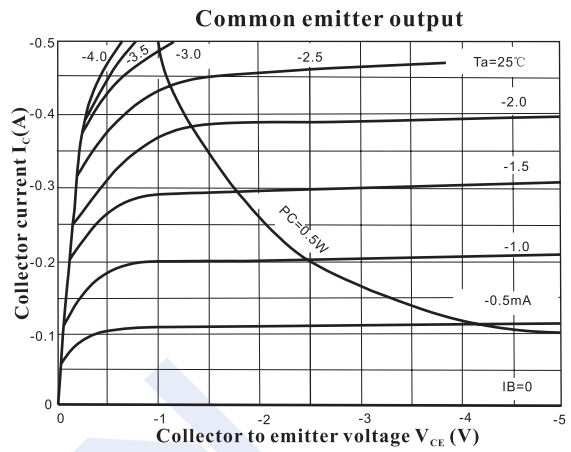
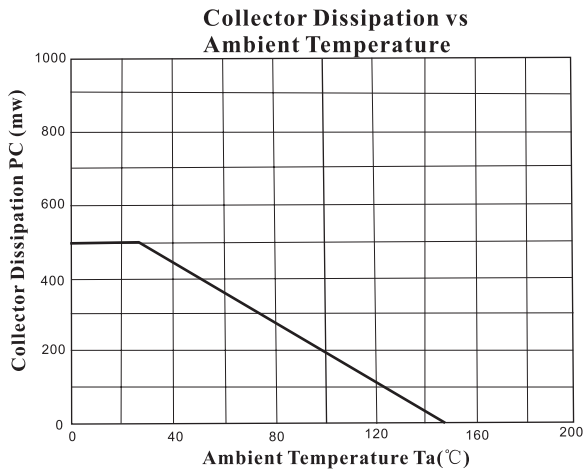
■ Classification of h_{FE}

Type	2SA1364-C	2SA1364-D	2SA1364-E
Range	55-110	90-180	150-300
Marking	CC	CD	CE

PNP Transistors

2SA1364

■ Typical Characteristics



PNP Transistors

2SA1364

■ Typical Characteristics

